L Number	Hits	Search Text	DB	Time stamp
1	7369	1 1 (007)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/05 16:23
2	1793	<pre>(((((((silicon near on insulator) (SOI))) and ((silicon near oxide) (sio."sub.2"))) and (silicon near (substrate base pad wafer))) and (silicon near layer)) and ((refractory near metal) (titanium near tungsten) (titanium near nitride))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/05 16:25

L Number	Hits	Search Text	DB	Time stamp
49	220768	((silicon near on insulator) (SOI))	USPAT;	2002/11/05 13:22
			US-PGPUB;	1
!	,		EPO; JPO;	
		i !	DERWENT;	
	05450	(//	IBM_TDB	2002/11/05 12:23
50	25450	(((silicon near on insulator) (SOI))) and ((silicon near oxide) (sio."sub.2"))	USPAT; US-PGPUB;	2002/11/05 13:23
		((Silicon hear oxide) (Sio. Sub.2))	EPO; JPO;	
			DERWENT;	i l
			IBM TDB	
51	12751	((((silicon near on insulator) (SOI))) and	USPAT;	2002/11/05 13:24
	S 19	((silicon near oxide) (sio."sub.2"))) and	US-PGPUB;	
		(silicon near (substrate base pad wafer))	EPO; JPO;	!
		V.V.	DERWENT;	į l
	7060		IBM_TDB	0000 (11 (05 12 20)
53	7369	,,,,,==================================	USPAT;	2002/11/05 13:32
		and ((silicon near oxide) (sio."sub.2"))) and (silicon near (substrate base pad	EPO; JPO;	i !
		wafer))) and (silicon near layer)	DERWENT;	1
	Δ	water,,, and torrieon hear rayer,	IBM TDB	
54	904	((((((silicon near on insulator) (SOI)))	USPAT;	2002/11/05 13:33
		and ((silicon near oxide) (sio."sub.2")))	US-PGPUB;	
		and (silicon near (substrate base pad	EPO; JPO;	
	W 9 1.1	wafer))) and (silicon near layer)) and	DERWENT;	
		(refractory near metal)	IBM TDB	<u> </u>